

DMP3056LDM-7 Datasheet



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DiGi Electronics Part Number DMP3056LDM-7-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number DMP3056LDM-7

Description MOSFET P-CH 30V 4.3A SOT-26

Detailed Description P-Channel 30 V 4.3A (Ta) 1.25W (Ta) Surface Moun

t SOT-26



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMP3056LDM-7	Diodes Incorporated
Series:	Product Status:
	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	4.3A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	45mOhm @ 5A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
2.1V @ 250μA	21.1 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	948 pF @ 25 V
FET Feature:	Power Dissipation (Max):
	1.25W (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
SOT-26	SOT-23-6
Base Product Number:	
DMD2056	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(ON) Max	I _D T _A = +25°C
-30V	45mΩ @ V _{GS} = -10V	-4.3A
-30 <i>V</i>	65mΩ @ V _{GS} = -4.5V	-3.3A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- · General purpose interfacing switches
- Power management functions
- Analog switches

Features

- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

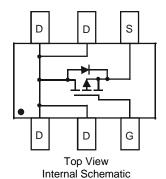
https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT26
- Package Material Molded Plastic, "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.016 grams (Approximate)



Top View



Ordering Information (Note 4)

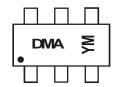
Part Number	Pac	king	
Fart Number	Package	Qty.	Carrier
DMP3056LDM-7	SOT26	3000	Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



DMA = Product Type Marking Code YM = Date Code Marking Y = Year (ex: J = 2022)M = Month (ex. 8 = August)

Date Code Key

Year	2008		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	V		J	K	L	М	N	0	Р	R	S	Т
	1			_			1	1				
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 5) \/- 10\/	Steady State T _A = +25°		ID	-4.3	Α
Continuous Drain Current (Note 5) $V_{GS} = -10V$ $t < 10s$ $T_A = +2$			I _D	-5.8	Α
Maximum Continuous Body Diode Forward Curre	ent (Note 5)		Is	-2.3	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)		I _{DM}	-13	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.25	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	100	°C/W
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.5	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State		RθJA	86	°C/W
Thermal Resistance, Junction to Case		Rejc	15.6	*C/VV
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Notes:

5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad.6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



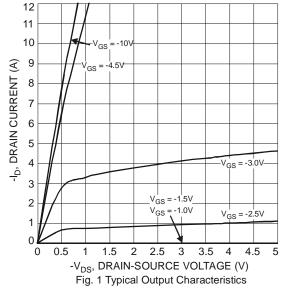
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
STATIC PARAMETERS (Note 7)								
Drain-Source Breakdown Voltage	BVDSS	-30	_	_	V	Vgs = 0V, ID = -250µA		
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	-1	μA	Vgs = 0V, Vps = -30V		
Gate-Body Leakage Current	Igss			±100 ±800	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$ $V_{GS} = \pm 25V, V_{DS} = 0V$		
Gate Threshold Voltage	Vgs(TH)	-1.0	_	-2.1	V	Vgs = Vps, Ip = -250µA		
Static Drain-Source On-Resistance	R _{DS(ON)}			45 65	mΩ	$V_{GS} = -10V, I_{D} = -5A$ $V_{GS} = -4.5V, I_{D} = -4.2A$		
Forward Transconductance	grs	_	8	_	s	$V_{DS} = -10V$, $I_{D} = -4.3A$		
Diode Forward Voltage	V_{SD}	-	_	-1.2	V	$V_{GS} = 0V$, $I_{S} = -1.7A$		
DYNAMIC PARAMETERS (Note 8)								
Input Capacitance		1	948	_	pF			
Output Capacitance	Coss	_	105	_	pF	V _G S = 0V, V _D S = -25V f = 1.0MHz		
Reverse Transfer Capacitance	Crss	_	100	_	pF	1 = 1.01/11/12		
SWITCHING CHARACTERISTICS (Note 8)								
Total Gate Charge	Qg		10.1	_	nC	$V_{DS} = -15V$, $V_{GS} = -4.5V$ $I_{D} = -6A$		
	Q_g	-	21.1	_		45)/)/ 40)/		
Gate-Source Charge	Qgs	-	2.8	_	nC	$V_{DS} = -15V, V_{GS} = -10V$ $I_{D} = -6A$		
Gate-Drain Charge	Q_{gd}	1	3.2	_		10 = -0A		
Gate Resistance	R_g	_	13.15	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$		
Turn-On Delay Time	t _{D(ON)}	_	10.2	_				
Rise Time	t _R		6.6	_		V _{DS} = -15V, V _{GS} = -10V		
Turn-Off Delay Time	tD(OFF)	_	50.1	_	ns	$I_D = -1A$, $R_g = 6.0\Omega$		
Fall Time	t _F		22.3	_				

Notes:

^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.





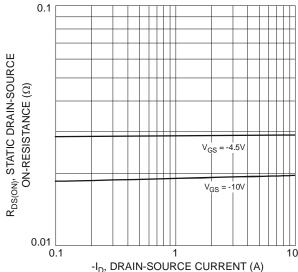


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

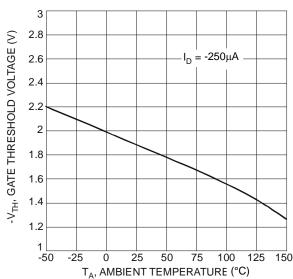
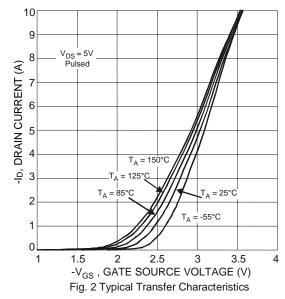


Fig. 5 Gate Threshold Variation vs. Ambient Temperature



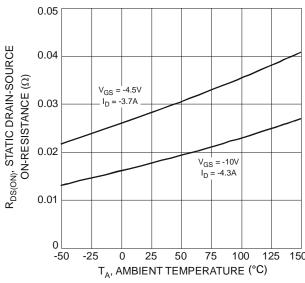
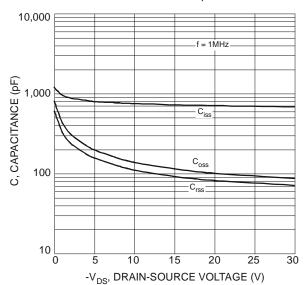


Fig. 4 Static Drain-Source On-Resistance vs. Ambient Temperature





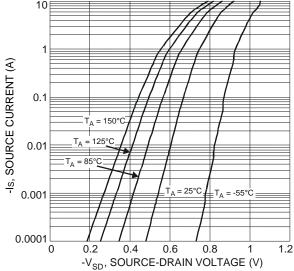
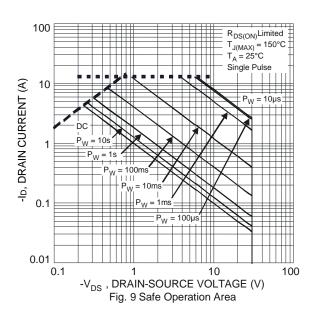


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage



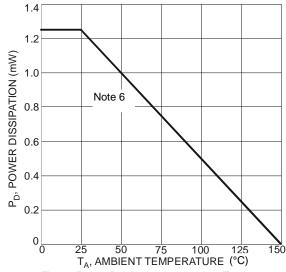


Fig. 11 Power Dissipation vs. Ambient Temperature

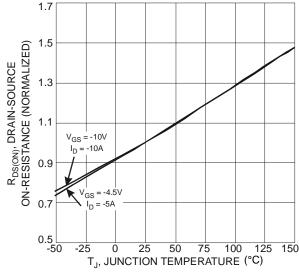
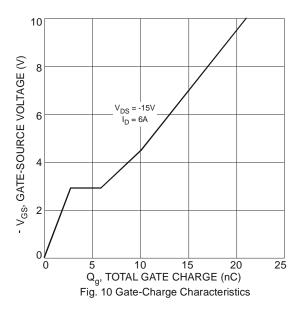


Fig. 8 On-Resistance Variation with Temperature





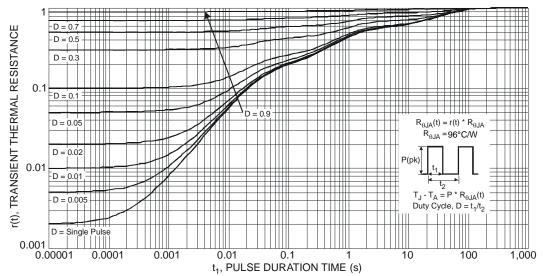


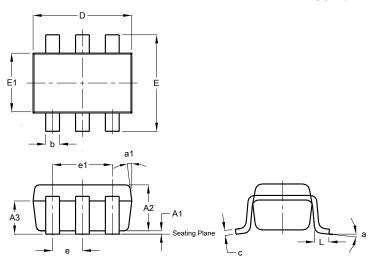
Fig. 12 Transient Thermal Response



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26

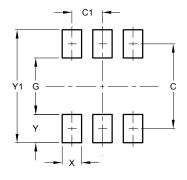


SOT26							
Dim	Min	Max	Тур				
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
A3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е	-	-	0.95				
e1	-	-	1.90				
E	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	-	-	8°				
a1	-	-	7°				
All	Dimen	sions	in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Υ	0.80
Y1	3.20



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